

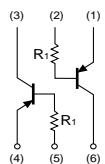
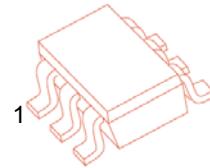


JIANGSU CHANGJIANG ELECTRONICS TECHNOLOGY CO., LTD

SOT-363 Plastic-Encapsulate Transistors

UMB4N dual digital transistors (PNP+PNP)**FEATURES**

Two DTA144T chips in a package.

Marking: B4**Equivalent circuit****SOT-363****Absolute maximum ratings ($T_a=25^\circ\text{C}$)**

| Symbol | Parameter | Value | Units |
|-----------|---------------------------|----------|-------|
| V_{CBO} | Collector-Base Voltage | -50 | V |
| V_{CEO} | Collector-Emitter Voltage | -50 | V |
| V_{EBO} | Emitter-Base Voltage | -5 | V |
| I_c | Collector Current | -100 | mA |
| P_D | Power Dissipation | 150 | mW |
| T_J | Junction Temperature | 150 | °C |
| T_{stg} | Storage Temperature | -55~+150 | °C |

ELECTRICAL CHARACTERISTICS ($T_a=25^\circ\text{C}$)

| Parameter | Symbol | Test conditions | Min | Typ | Max | Unit |
|--------------------------------------|----------------------|--|-----|-----|------|------|
| Collector-base breakdown voltage | $V_{(BR)CBO}$ | $I_C=50\mu\text{A}, I_E=0$ | -50 | | | V |
| Collector-emitter breakdown voltage | $V_{(BR)CEO}$ | $I_C=-1\text{mA}, I_B=0$ | -50 | | | V |
| Emitter-base breakdown voltage | $V_{(BR)EBO}$ | $I_E=-50\mu\text{A}, I_C=0$ | -5 | | | V |
| Collector cut-off current | I_{CBO} | $V_{CB}=-50\text{V}, I_E=0$ | | | -500 | nA |
| Emitter cut-off current | I_{EBO} | $V_{EB}=-4\text{V}, I_C=0$ | | | -500 | nA |
| DC current transfer ration | h_{FE} | $V_{CE}=-5\text{V}, I_C=-1\text{mA}$ | 100 | | 600 | |
| Collector-emitter saturation voltage | $V_{CE(\text{sat})}$ | $I_C=-10\text{mA}, I_B=-1\text{mA}$ | | | -0.3 | V |
| Transition frequency | f_T | $V_{CE}=-10\text{V}, I_C=-5\text{mA}, f=100\text{MHz}$ | | 250 | | MHz |
| Input resistance | R_1 | | - | 7 | 13 | KΩ |